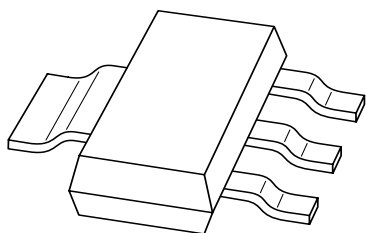


DATA SHEET



BCP54; BCP55; BCP56 NPN medium power transistors

Product specification
Supersedes data of 2001 Oct 10

2003 Feb 06

NPN medium power transistors

BCP54; BCP55; BCP56

FEATURES

- High collector current
- 1.3 W power dissipation.

APPLICATIONS

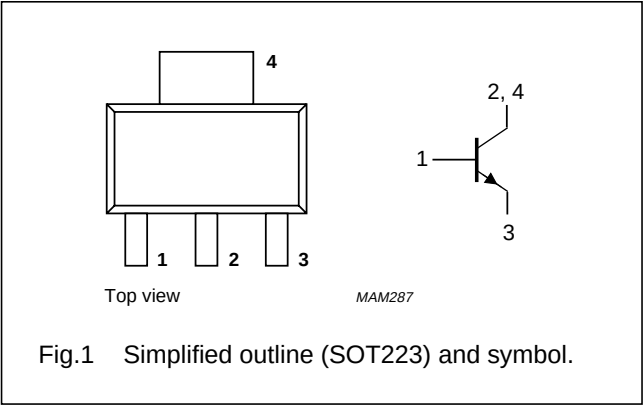
- General purpose medium power DC applications
- Low and medium frequency AC applications
- Peripheral drivers
- Linear voltage regulators and battery chargers.

DESCRIPTION

NPN medium power transistor in a SOT223 plastic package. PNP complements: BCP51, BCP52 and BCP53.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	80	V
I_C	collector current (DC)	1	A
I_{CM}	peak collector current	1.5	A

NPN medium power transistors

BCP54; BCP55; BCP56

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BCP54		–	45	V
	BCP55		–	60	V
	BCP56		–	100	V
V _{CEO}	collector-emitter voltage	open base			
	BCP54		–	45	V
	BCP55		–	60	V
	BCP56		–	80	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	1	A
I _{CM}	peak collector current		–	1.5	A
I _{BM}	peak base current		–	0.2	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	1.33	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	94	K/W
R _{th j-s}	thermal resistance from junction to soldering point		13	K/W

Note

1. Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

NPN medium power transistors

BCP54; BCP55; BCP56

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 125\text{ }^{\circ}\text{C}$	–	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 5\text{ mA}; V_{CE} = 2\text{ V}$	63	–	–	
		$I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$	63	–	250	
		$I_C = 500\text{ mA}; V_{CE} = 2\text{ V}$	40	–	–	
h_{FE}	DC current gain BCP54-10; BCP55-10; BCP56-10 BCP54-16; BCP55-16; BCP56-16	$I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$		–		
			63	–	160	
			100	–	250	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 50\text{ mA}$	–	–	500	mV
V_{BE}	base-emitter voltage	$I_C = 0.5\text{ A}; V_{CE} = 2\text{ V}$	–	–	1	V
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	–	130	–	MHz
$\frac{h_{FE1}}{h_{FE2}}$	DC current gain ratio of the complementary pairs	$ I_C = 150\text{ mA}; V_{CE} = 2\text{ V}$	–	–	1.6	

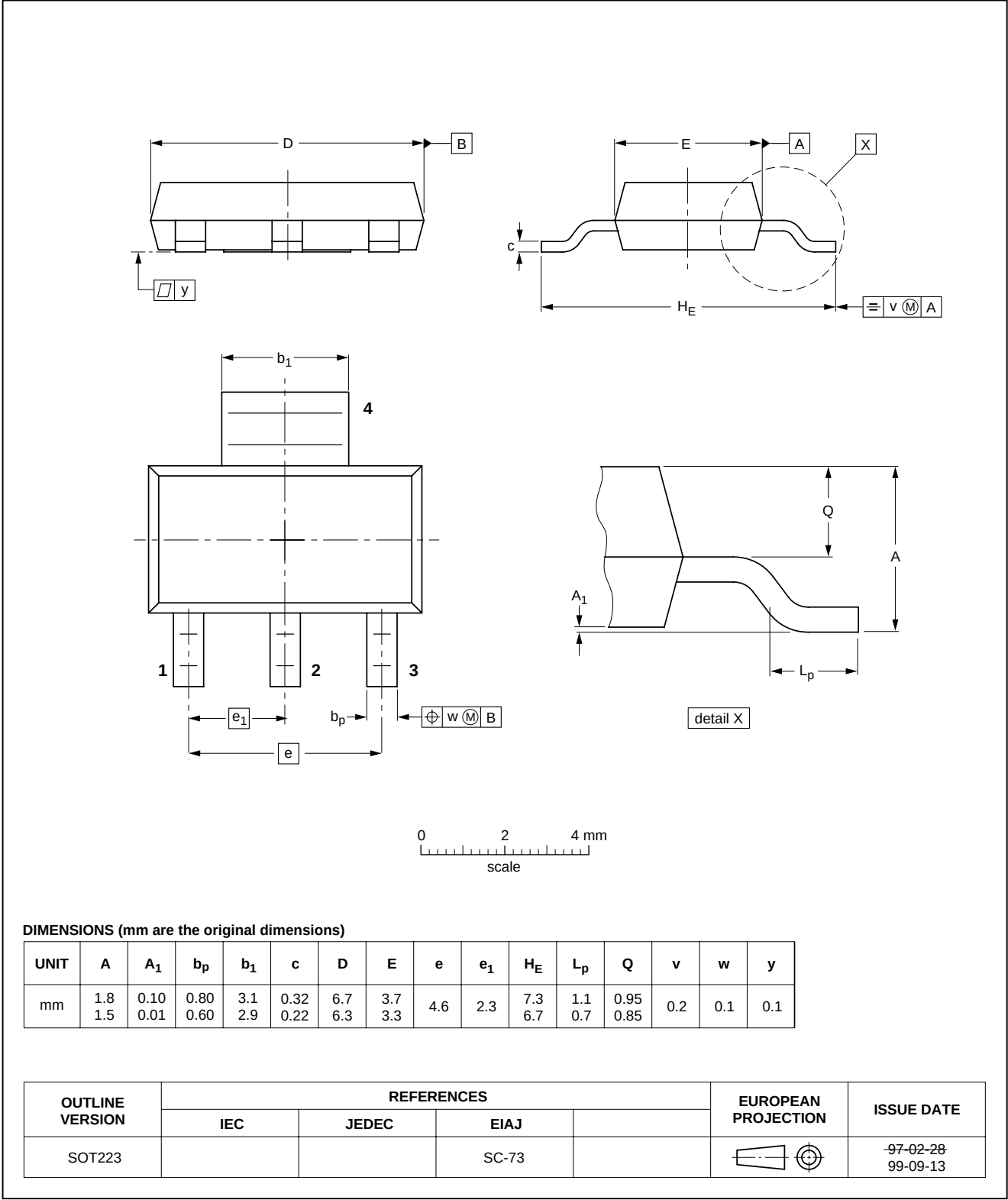
NPN medium power transistors

BCP54; BCP55; BCP56

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



NPN medium power transistors

BCP54; BCP55; BCP56

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

1. Please consult the most recently issued data sheet before initiating or completing a design.
2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.
3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

DISCLAIMERS

Life support applications — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no licence or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

NPN medium power transistors

BCP54; BCP55; BCP56

NOTES

Philips Semiconductors – a worldwide company

Contact information

For additional information please visit **<http://www.semiconductors.philips.com>**. Fax: **+31 40 27 24825**

For sales offices addresses send e-mail to: **sales.addresses@www.semiconductors.philips.com**.

© Koninklijke Philips Electronics N.V. 2003

SCA75

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

613514/05/pp8

Date of release: 2003 Feb 06

Document order number: 9397 750 10763

Let's make things better.

**Philips
Semiconductors**



PHILIPS